

FORM PTO-1449

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09/944,186INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

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APPLICANT
Atsushi YAMAGUCHI et al.FILING DATE
September 4, 2001GROUP
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA						

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

	DOCUMENT NO.	PUBL. DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES NO
AI	A 11-307866	11/99	JP			with English abstract
AJ	A 11-340580	12/99	JP			with English abstract
AK						

OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication)

AL	Shuji NAKAMURA, "Current Status and Future Prospects of InGaN-Based Laser Diodes," JSAP International, Jan. 2000, Tokushima, Japan, pp. 5-17.
AM	Masaru KURAMOTO et al., "Towards a Durable InGaN MQW LD--Room Temperature CW Operation of InGaN MQW Laser," NEC Res. & Develop., V. 41, January 2000, pp. 74-86.
AN	Shuji NAKAMURA et al., "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices," Jpn. J. Appl. Phys., V. 36, 1997, pp. L1568-L1571.
AO	Akira USUI et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy," Jpn. J. Appl. Phys., V. 36, 1997, pp. L899-L902.
AP	Shigefusa CHICHIBU, "Spatially Resolved Cathodoluminescence Spectra of InGaN Quantum Wells," Appl. Phys. Lett. 71, 1997, pp. 2346-2348.
AQ	W. W. CHOW et al., "Microscopic Theory of Gain for an InGaN/AlGaN Quantum Well Laser," Appl. Phys. Lett. 71, 1997, pp. 2608-2610.
AR	A. Atsushi YAMAGUCHI et al., "Optical Recombination Processes in High-Quality GaN Films and InGaN Quantum Wells Grown on Facet-Initiated Epitaxial Lateral Overgrown GaN Substrates," Jpn. J. Appl. Phys., V. 39, 2000, pp. 2402-2406.
AS	G. Martin et al., "Valence-Band Discontinuities of Wurtzite GaN, AlN, and InN Heterojunctions Measured by X-Ray Photoemission Spectroscopy," Appl. Phys. Lett. 68, 1996, pp. 2541-2543.
AT	

EXAMINER

Shounaghi

DATE CONSIDERED

2-19-04

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.